# SG2M1K0170BJ

**TriQSiC™ 1700V Silicon Carbide Power MOSFET G2**

## Features

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## Benefits

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# 1 Maximum ratings

**Table 2 Maximum rating**

| Symbol | Parameter | Value | Unit | Test Conditions | Note |
|---|---|---|---|---|---|

# SG2M1K0170BJ

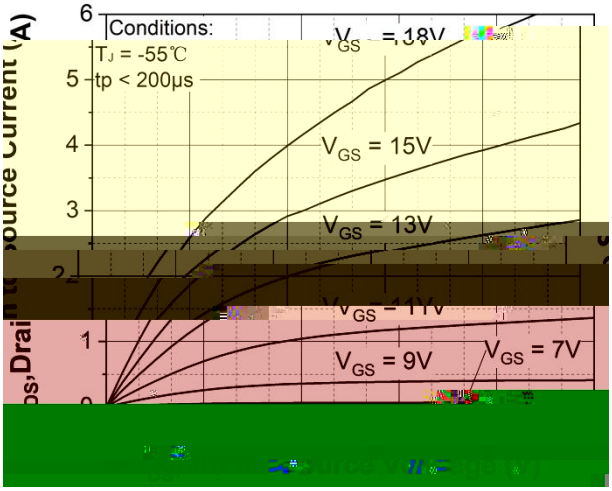
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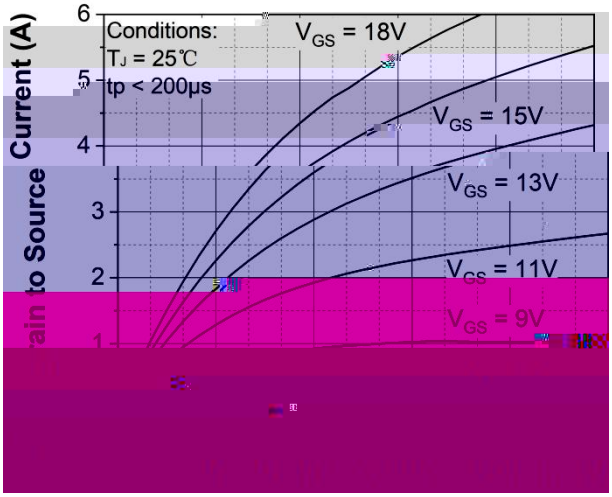
## 2.3 Switching characteristics

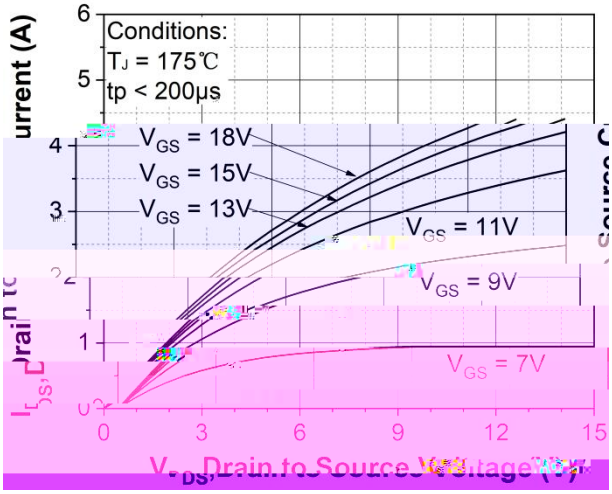
**Table 6 Dynamic characteristics**

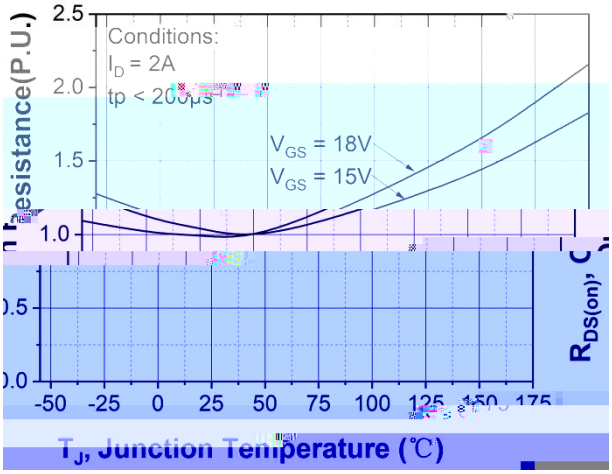
| Symbol | Parameter | Min. | Typ. | Max. | Unit | Test Conditions | Note |
|---|---|---|---|---|---|---|---|

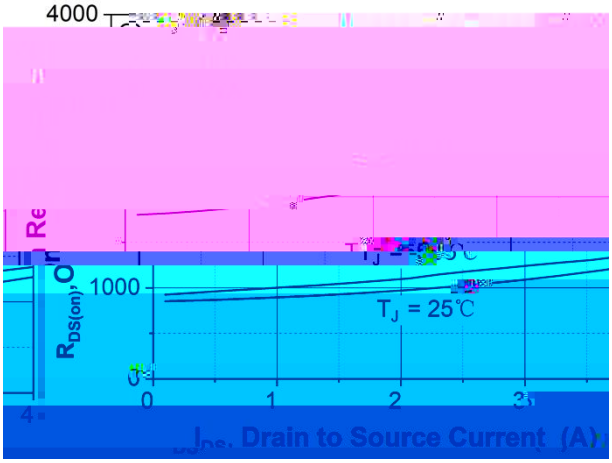
## 3 Electrical characteristic diagrams

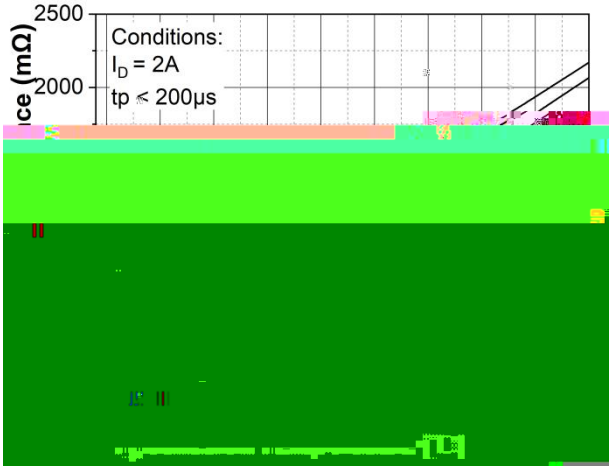


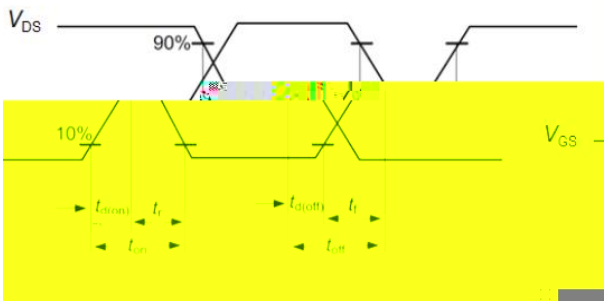



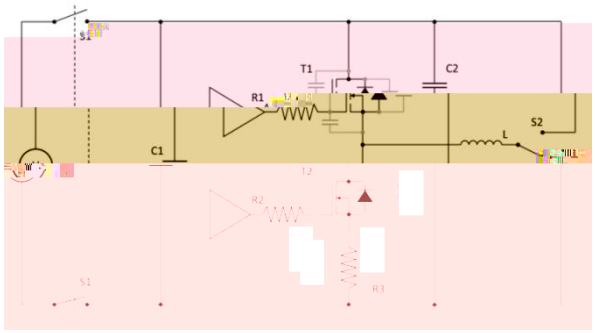
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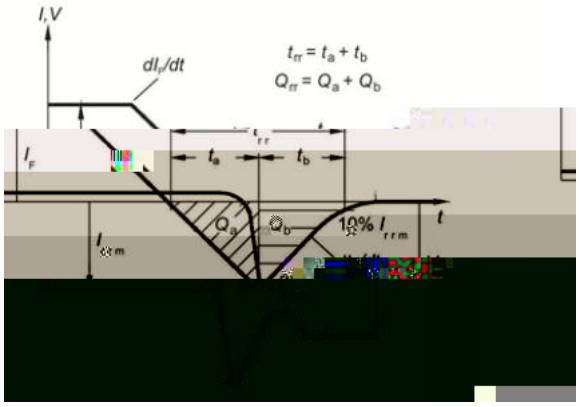
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# SG2M1K0170BJ

# 5 Test conditions



# SG2M1K0170[illegible]J

**1700V SiC Power MOS[illegible]T**

## Revision history

| Document version | Date of release | Document stage | Description of changes |
|---|---|---|---|
| V01_00 | 2025-07-11 | —— | —— |
| V01_01 | 2025-09-08 | —— | —— |
| V01_02 | 2025-12-30 | Final | —— |
| | | | |

## Attention

**Rohs compliance**

**REACH compliance**

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